

# ON Semiconductor

## Is Now

# onsemi™

To learn more about onsemi™, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

**onsemi** and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

# NGTD17T65F2

## IGBT Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

### Features

- Extremely Efficient Trench with Field Stop Technology
- Low  $V_{CE(sat)}$  Loss Reduces System Power Dissipation

### Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^\circ\text{C}$	$V_{CE}$	650	V
DC Collector Current, limited by $T_{J(max)}$	$I_C$	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, pulse}$	160	A
Gate–Emitter Voltage	$V_{GE}$	$\pm 20$	V
Maximum Junction Temperature	$T_J$	$-55$ to $+175$	$^\circ\text{C}$
Short Circuit Withstand Time, $V_{GE} = 15\text{ V}$ , $V_{CE} = 500\text{ V}$ , $T_J \leq 150^\circ\text{C}$	$T_{SC}$	5.0	$\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.
2.  $T_{pulse}$  limited by  $T_{jmax}$ , 10  $\mu\text{s}$  pulse,  $V_{GE} = 15\text{ V}$ .

### MECHANICAL DATA

Parameter	Value	Unit
Die Size	3915 x 4115	$\mu\text{m}^2$
Emitter Pad Size	See die layout	$\mu\text{m}^2$
Gate Pad Size	585 x 600	$\mu\text{m}^2$
Die Thickness	3	mils
Wafer Size	150	mm
Top Metal	4 $\mu\text{m}$ AISI	
Back Metal	2 $\mu\text{m}$ TiNiAg	
Max possible chips per wafer	778	
Passivation frontside	Oxide–Nitride	
Reject ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28 $^\circ\text{C}$ , 30–65%RH	Type: Die on tape in ring–pack Storage time: < 3 months	

### ORDERING INFORMATION

Device	Inking?	Shipping
NGTD17T65F2WP	Yes	Bare Wafer on Tape
NGTD17T65F2SWK	Yes	Sawn Wafer on Tape

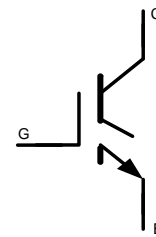


ON Semiconductor®

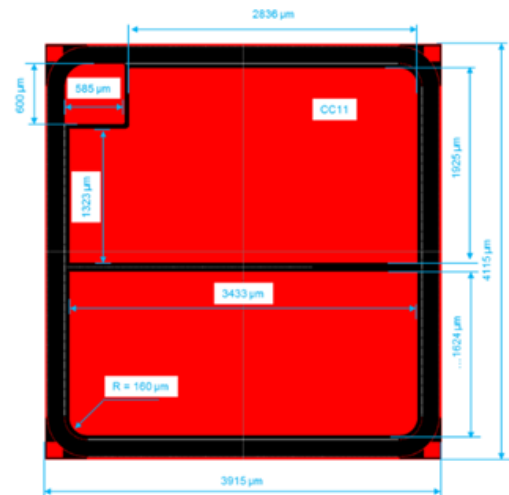
[www.onsemi.com](http://www.onsemi.com)

$V_{RCE} = 650\text{ V}$   
 $I_C = \text{Limited by } T_{J(max)}$

IGBT DIE



DIE OUTLINE



# NGTD17T65F2

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

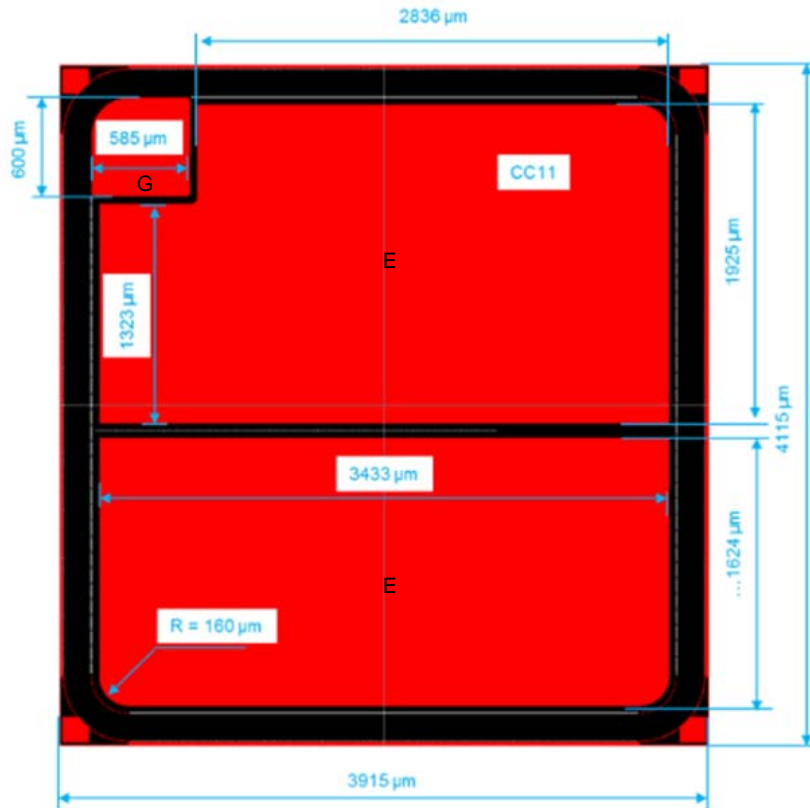
Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>STATIC CHARACTERISTICS</b>						
Collector–Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	650			V
Collector–Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$	$V_{CE(sat)}$		1.7	2.0	V
Gate–Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector–Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	$I_{CES}$			0.5	mA
Gate Leakage Current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$			200	nA

## DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$		4060		pF
Output Capacitance		$C_{oes}$		179		pF
Reverse Transfer Capacitance		$C_{res}$		115		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## DIE LAYOUT



E = Emitter pad  
G = Gate pad  
All dimensions in  $\mu\text{m}$

## Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

### Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

